3DD57, 3DD60

NPN Silicon Low Frequency High Power Transistor

Features:

1. Using triple-diffusion,low resistance liner process.Heavy out-put Current,small saturation voltage drop. Excellent out-put characteristic.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, power amplify,power adjustment,DC conversion.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications				
			3DD57			3DD60	
			A	B	C	D	E
Collector-Emitter Voltage	V_{CEO}	V	30	50	80	110	150
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	30	50	80	110	150
			3DD57: I_C=3mA			3DD60: I_C=5mA	
Emitter-Base Voltage	V_{EBO}	V	3			3	
Max. Collector Current	I_{CM}	A	1.5			2.5	
Max. Collector Dissipation	P_{CM}	W	10 (T_C≤75°C)			25 (T_C≤75°C)	
Junction Temperature	T_{jm}	°C	175				
Storage Temperature	T_{stg}	°C	-55~+175				
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:1.0 (V_{CE}=20V)			Max.:1.5 (V_{CE}=20V)	
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:1.0 (I_C=0.75A,I_B=0.15A)			Max.:1.2 (I_C=1.25A,I_B=0.25A)	
DC Current Gain	h_{FE}		Min.:10 (I_C=0.75A,I_B=0.15A)			Min.:10 (V_{CE}=5V,I_C=1.25A)	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥3 (I_E=5mA)			≥3 (I_E=10mA)	

h_{FE} Colored:

Color	Brown	Red	Orange
h_{FE}	10~20	20~30	≥30

Outline and Dimensions:

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